

Characterization of thin n-in-p planar pixel sensors and status of the new active edge pixel production

Wednesday, November 19, 2014 1:55 PM (20 minutes)

N-in-p planar pixel sensors with an active thickness of 200 μm produced at CiS, and 100-200 μm thin active/slim edge sensor devices, produced at VTT in Finland have been interconnected to ATLAS FE-I3 and FE-I4 read-out chips and irradiated in Ljubljana, Los Alamos and KIT up to a fluence of $1.4 \times 10^{16} \text{ n}_{\text{eq}}/\text{cm}^2$. Charge collection properties and tracking efficiencies are studied to investigate their possible applications in the inner layers of the ATLAS pixel detectors at HL-LHC. An update on the status of the new production of active edge pixels at ADVACAM is given.

Presenter: PASCHEN, Botho Albrecht (Max-Planck-Institut fuer Physik (Werner-Heisenberg-Institut) (D))

Session Classification: Segmented Sensors, Test Beams and Detector Systems